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PTO/SB/08A (10-01)
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

| Complete if Known | |
|---|---|
| Application / Control Number | Unknown 10/726,115 |
| Filing Date | November 12, 2003 |
| First Named Inventor | Kevin T. Look |
| Art Unit | Unknown 2891 |
| Examiner Name | Unknown |
| Attorney Docket Number | X-1144 US |

## U.S. PATENT DOCUMENTS

| Examiner Initials * | Cite No.[1] | Document Number Number - Kind Code (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| SJF | | US- 6,496,416 B1 | 12-17-02 | Look | |
| SJF | | US- 10/283,736 | | Look | Filed 10/29/02 |
| SJF | | US- 10/693,467 | | Look | Filed 10/24/03 |
| SJF | | US- 10/693,468 | | Look | Filed 10/24/03 |
| SJF | | US- 10/693,219 | | Look | Filed 10/24/03 |
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| Examiner Initials * | Cite No.[1] | Foreign Patent Document Country Code[3] -Number[4] -Kind Code[5] (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T[6] |
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| Examiner Signature | Steve Fall | Date Considered | 7/19/05 |
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Applicant's unique citation designation number (optional). [2] See Kinds of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 2

| Complete if Known | |
|---|---|
| Application / Conf. N. | Unknown / |
| Filing Date | November 12, 2003 |
| First Named Inventor | Kevin T. Look |
| Art Unit | Unknown |
| Examiner Name | Unknown |
| Attorney Docket Number | X-1144 US |

## OTHER – NON PATENT LITERATURE DOCUMENTS

| Examiner Initials * | Cite No.[1] | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T[2] |
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